Claims

1. An apparatus configured to form an epitaxial layer on a substrate comprising:

a gas delivery system coupled to an epitaxial deposition chamber, the gas delivery system comprising:

a gas conduit has a first end and a second end, the first end coupled to a gas panel and a second end branched out to include an auxiliary inner dopant inlet and an auxiliary outer dopant inlet, wherein the auxiliary inner dopant inlet and the auxiliary outer dopant inlet are independently controlled when implementing in the epitaxial deposition chamber, wherein the auxiliary inner dopant inlet is coupled to couple to an inner inlet port formed in the epitaxial deposition chamber, and wherein the inner inlet port is formed approximate to a center of the epitaxial deposition chamber and the outer inlet port is formed approximate to a side of the epitaxial deposition chamber.